Erratum to "Quantum compact model for thin-body double-gate Schottky barrier MOSFETs"

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The statement for the third paragraph of the right column of page 3079 (Chinese Physics B, 2008, Vol. 17, No. 8, pp. 3077–3082)[1] is inappropriate. This paragraph should be restated as follows.

For the calculation by using the model, a Riemann sum for integrating expressions (6) and (7) is used and the upper limit in expression (6) is set to a finite value, as discussed in Ref. [2]. Furthermore, $V_{\rm ds}$ must also be included to account for the difference in F–D distribution between the source and the drain at a given energy.

References

[1] Luan S Z and Liu H X 2008 *Chin. Phys.* B **17** 3079

[2] Reinaldo A V 2006 *IEEE Trans. Electron Device* **53** 1596